arXiv:1301.5182v1 [cond-mat.mes-hall] 22 Jan 2013

Josephson junction on one edge of a two dimensional topological insulator affected by magnetic impurity

Shu-feng Zhang, Wei Zhu, and Qing-feng Sun*
Institute of Physics, Chinese Academy of Sciences, Beijing 100190, China

Current-phase relation in a Josephson junction formed by putting two s-wave superconductors on the same edge of a two dimensional topological insulator is investigated. We consider the case that the junction length is finite and magnetic impurity exists. The similarity and difference with conventional Josephson junction is discussed. The current is calculated in the semiconductor picture. Both the 2π- and 4π-period current-phase relations $(I_{2\pi}(\phi), I_{4\pi}(\phi))$ are studied. There is a sharp jump at $\phi = \pi$ and $\phi = 2\pi$ for $I_{2\pi}$ and $I_{4\pi}$ respectively in the clean junction. For $I_{2\pi}$, the sharp jump is robust against impurity strength and distribution. However for $I_{4\pi}$, the impurity makes the jump at $\phi = 2\pi$ smooth. The critical (maximum) current of $I_{2\pi}$ is given and we find it will be increased by asymmetrical distribution of impurity.

PACS numbers: 74.45.+c, 74.78.Na, 71.10.Pm, 74.78.Fk

I. INTRODUCTION

Recently the topological insulator (TI) has excited great interest in the condensed-matter community.[1,2] The unique feature of TI is the existence of edge states (or surface states) which is protected by time reversal symmetry. The edge state of a two dimensional (2D) TI can be considered approximately as a 1D mental. But since spin and momentum direction of carriers is locked together owing to strong spin-orbit coupling, it's only half of the ordinary electron gas. This helical property is robust against nonmagnetic impurity due to its topological origin. If the edge state is in contact with a superconductor, a topological superconducting edge state will form in the interface because of proximity effect.[3,4] And it can be viewed as a 1D topological superconductor (TS). Therefore it's able to construct a Josephson junction on one edge of the 2D TI.

Experimentally, the edge state in HgTe/CdTe quantum wells,[5] in InAs/GaSb quantum wells,[6] and surface state in Bi_2Se_3 systems[7] have been observed. The superconducting proximity effect and Andreev reflection in InAs/GaSb quantum wells and Bi_2Se_3 systems coupling to superconducting electrode have been demonstrated.[8,9]

The conventional superconductor-normal metal-superconductor (SNS) junction has been investigated in detail in the last three decades.[10–14] Since the superconductor-TI-superconductor (STiS) junction is only half of the SNS junction, the corresponding Andreev bound state[10] and current-phase relation are similar for the clean junction if we suppose quasiparticles distribute thermodynamically (2π-period current case).[15] However for STiS junction, a 4π-period current-phase $(I_{4\pi}(\phi))$ relation (fractional Josephson effect) may arise if the thermodynamical distribution is partially destroyed while superconducting phase difference is changed adiabatically.[4,16] The effect of nonmagnetic impurity and magnetic impurity is identical for the SNS junction due to spin degeneracy. However for the STiS junction only magnetic impurity can lead to a backscattering owing to time reversal symmetry. In dirty junctions magnetic impurity contributes another significant difference, the extra π phase shift for hole reflection.[17] As a result even the 2π-period current $(I_{2\pi}(\phi))$ and Andreev bound states of STiS junction would be quite different from those of the SNS junction.

However in earlier work,[4,16–25] only short STiS junction (junction length L far less than the superconductor coherent length ξ_0) is studied. And it's only very recently we notice that the work by Beenakker *et al.*[26] discusses the finite length clean junction. To the best knowledge of us, a study of the finite length STiS junction affected by magnetic impurity is still missing. That is the gap we want to fill here.

In this article both the 2π-period and 4π-period current-phase relation is calculated. There is a sharp jump at $\phi = \pi$ and $\phi = 2\pi$ for $I_{2\pi}$ and $I_{4\pi}$ respectively in the clean junction. For $I_{2\pi}$, the sharp jump at $\phi = \pi$ is robust against impurity strength and distribution. However for $I_{4\pi}$, the impurity makes the jump at $\phi = 2\pi$ smooth. The critical current and shape of current-phase characteristics are greatly influenced by junction length.

The rest of the paper is organized as follows. In Sec. II, we describe the model and give the analytical results. In Sec. III, the numerical results and analysis are given. In Sec. IV, we give a brief conclusion. In Appendix A, we give the reason of the similarity between STiS junction and conventional SNS junction. In Appendix B and C, we derive the current operator and give the detail of the calculation.

II. MODEL AND ANALYTICAL RESULTS

Two s-wave superconductors are in intimate contact with one edge of 2D TI. Because of the proximity effect, a 1D TS forms in the interface. Then we have a STiS Josephson junction on one edge of the 2D TI.[27] The effective Hamiltonian of the edge state is given as $H_0 = v_F \sigma_3 p_x$, in which $p_x = -i\hbar\partial_x$, $\sigma_{1,2,3}$ are Pauli matrices acting in the spin space and v_F is the velocity of the edge states.[2] Proximity effect contributes a paring term, then the Hamiltonian of the 1D TS is given as,[4]

$$H = \int dx \psi^\dagger (H_0 - \mu)\psi + \Delta \psi_\uparrow^\dagger \psi_\downarrow^\dagger + \Delta^* \psi_\downarrow \psi_\uparrow \tag{1}$$

in which $\psi = (\psi_\uparrow, \psi_\downarrow)^T$, $\psi_\uparrow$ ($\psi_\downarrow$) annihilates a right (left)-moving electron. $\Delta = \Delta_0 e^{i\phi'}$ is the paring potential, $\Delta_0 = |\Delta|$ and ϕ' is the phase of the superconductor. In Nambu representation $\Psi = (\psi_\uparrow, \psi_\downarrow, \psi_\downarrow^\dagger, -\psi_\uparrow^\dagger)^T$, with $i\hbar\partial_t \Psi = H_{BdG}\Psi$ we derive the Bogoliubov-de Gennes (BdG) Hamiltonian[4,28]

$$H_{BdG} = v_F p_x \sigma_3 \tau_3 - \mu\tau_3 + \Delta_0[cos(\phi')\tau_1 - sin(\phi')\tau_2], \tag{2}$$

where μ is the chemical potential and $\tau_{1,2,3}$ are Pauli matrices mixing the ψ and $\psi^\dagger$ blocks of Ψ. Particle hole symmetry is expressed as $\{H_{BdG}, \Xi\} = 0$, in which $\Xi = \sigma_2\tau_2 K$ and K is the complex conjugation operator. As a result these states are not independent. For an infinite TS the dispersion relation is $\epsilon = \pm\sqrt{\hbar^2 v_F^2 (k \pm k_F)^2 + |\Delta|^2}$, in which $\mu = \hbar v_F k_F$. And we neglect the self-consistency condition of Δ.[28] For the junction considered here, $\Delta = \Delta_0 e^{i\phi_1}\theta(-x) + \Delta_0 e^{i\phi_2}\theta(x - L)$ where L is the length of the junction.

We include a region with magnetic impurity by adding a scattering term $M\sigma_1\theta(x - L_1)\theta(L_2 - x)$ in H_{BdG}. The magnetic impurity can change the direction of particles, which can be described by the scattering matrix for electrons and holes

$$S_e = \begin{pmatrix} r & t \\ t & -r^* t/t^* \end{pmatrix} \quad and \quad S_h = \begin{pmatrix} -r^* & t^* \\ t^* & rt^*/t \end{pmatrix} \tag{3}$$

We denote the reflection coefficient $R = |r|^2$ and transition coefficient $T = |t|^2$. For simplicity, we have assumed that R is a constant independent of energy and the length of the impurity region. Under this assumption the effect of the length of the impurity region is equivalent to replacing the junction length L with an effective length $L' = L - (L_2 - L_1)$, and in the following we abbreviate L' to L. Comparing with SNS junction,[29] there is an extra π phase shift for hole reflection, and that's the origin of difference between STiS and SNS junction in Andreev bound states and $I_{2\pi}$ (see Appendix A for an explanation).

Incident particles with energy ϵ will be reflected at the superconductor-normal interface.[30] For SNS junction, it can occur both the Andreev and normal reflections at the interface. But for STiS junction, only the quantum Andreev reflection occurs at the interface.[8,31,32] If $|\epsilon| < \Delta_0$, incident particles will be reflected completely, therefore Andreev bound states will form.[10] Solve the BdG equation, then we obtain the energy level equation of Andreev bound states. For clean junction

$$-2arccos(\frac{\epsilon}{\Delta_0}) + \frac{\epsilon}{\Delta_0}\frac{L}{\xi_0} = \pm\phi + 2\pi n \tag{4}$$

where $\xi_0 = \hbar v_F/(2\Delta_0)$ is the superconducting coherent length, $\phi = \phi_2 - \phi_1$ is the phase difference and $n = 0, \pm1, \pm2, \ldots$. The second term on the left side of Eq.(4) is equal to $(k_e - k_h)L$, where k_e (k_h) is the wave vector of the right-moving electron (left-moving hole) with energy ϵ. Then we can interpret Eq.(4) in terms of Bohr-Sommerfeld quantization of the periodic electron-hole orbits in the TI region.[33] In the presence of impurity Andreev bound state is given as

$$-2arccos(\frac{\epsilon}{\Delta_0}) + \frac{\epsilon}{\Delta_0}\frac{L}{\xi_0} = \alpha \tag{5}$$

in which the phase difference is changed to α,

$$cos(\alpha) = Tcos(\phi) - R\,cos(\frac{\epsilon}{\Delta_0}\frac{L - 2L_1}{\xi_0}) \tag{6}$$

which is different from that of the SNS junction.[11]

The Josephson current $I(\phi)$ induced by the superconducting phase contains two parts, the discrete current $I_d(\phi)$ and the continuous current $I_c(\phi)$ carried by quasiparticles occupying Andreev bound states and continuous energy spectrum respectively. To compute the current, we suppose the system is nearly in thermodynamic equilibrium. Because the current is constant, we can solve the wave function and then obtain the average value of current operator in the TI region. The current due to the scattering state (the eigenstate of junction Hamiltonian) $\varphi = (u(x), u'(x), v(x), v'(x))^T$ with eigenvalue ϵ is

$$J = ev_F[(|u|^2 + |v|^2 - |u'|^2 - |v'|^2)f(\epsilon) - |v|^2 + |v'|^2] \tag{7}$$

where e is the electron charge and $f(\epsilon)$ is the Fermi distribution function. The last two terms describe the current carried by the "vacuum" (spin-down band and spin-up band filled by electrons) on which we can create quasiparticles occupying the ground state of H_{BdG} to obtain the superconducting ground state.[34] There is an alternative statistical method by which current is the derivative of free energy. In this article we use the wave function method to calculate the continuous current and the quantum statistical method for the discrete current. In appendix B and C we give the calculation detail and prove results according to both methods are equivalent for the discrete current.

The discrete current can be written as $I_d(\phi) = \sum_n I_n(\phi)f(\epsilon_n)$, where $I_n(\phi)$ is the current carried by the quasiparticle occupying Andreev bound state with eigenvalue ϵ_n. According to the quantum statistical method, the effective current due to Andreev bound state with eigenvalue ϵ_n is $I_n(\phi) = \frac{e}{\hbar}\frac{d\epsilon_n}{d\phi}$ (derived in Appendix C). For dirty junction,

$$\begin{aligned} I_n(\phi) &= \frac{1}{2}\frac{ev_F}{L + 2\xi(\epsilon_n)}\frac{Tsin(\phi)}{sin(\alpha)}\frac{1}{\gamma} \\ \gamma &= 1 + \frac{\hbar}{2e\Delta_0}\frac{ev_F}{L + 2\xi(\epsilon_n)}\frac{R}{sin(\alpha)}\frac{L - 2L_1}{\xi_0} \\ &\times\ sin(\frac{\epsilon_n(L - 2L_1)}{\Delta_0\xi_0}) \end{aligned} \tag{8}$$

For clean junction,

$$I_j^{\pm}(\phi) = \pm\frac{1}{2}\frac{ev_F}{L + 2\xi(\epsilon_j^{\pm})} \tag{9}$$

where $\xi(\epsilon) = \xi_0\frac{\Delta_0}{\sqrt{\Delta^2-\epsilon^2}}$ is the energy dependent coherent length.

For a short junction ($L << \xi_0$), it's enough to consider discrete current only, because the continuous current is of the order of L/ξ_0. However for a long junction the continuous current can not be neglected. To calculate $I_c(\phi)$, we first construct the scattering state for an incident particle having energy ϵ, and then apply the current formula given by Eq.(7). And we take the semiconductor picture (both the positive and negative solutions of BdG equation are used). The detail of constructing scattering states and computing current is similar to Ref.11, and some detail is given in Appendix B. Results are given below. For clean junction,

$$\begin{aligned} I_c(\phi) &= \frac{e}{h}T(\int_{-\infty}^{-\Delta_0} + \int_{\Delta_0}^{\infty})d\epsilon f(\epsilon)|u_0^2 - v_0^2| \\ &\times [\frac{1}{D(\epsilon,-\phi)} - \frac{1}{D(\epsilon,\phi)}] \end{aligned} \tag{10}$$

For dirty junction,

$$\begin{aligned} I_c(\phi) &= \frac{e}{h}T\int d\epsilon f(\epsilon)|u_0^2 - v_0^2|\frac{sin(\phi)}{sin(\alpha)} \\ &\times [\frac{1}{D(\epsilon,-\alpha)} - \frac{1}{D(\epsilon,\alpha)}] \end{aligned} \tag{11}$$

in which

$$\begin{aligned} D(\epsilon,\alpha) &= u_0^4 + v_0^4 - 2u_0^2v_0^2cos(\frac{\epsilon L}{\Delta_0\xi_0} + \alpha) \\ 2u_0^2 &= 1 + \frac{\sqrt{\epsilon^2 - \Delta_0^2}}{\epsilon} \\ 2v_0^2 &= 1 - \frac{\sqrt{\epsilon^2 - \Delta_0^2}}{\epsilon}, \quad u_0v_0 = \frac{\Delta_0}{2\epsilon} \end{aligned} \tag{12}$$

III. NUMERICAL RESULTS AND ANALYSIS

For the short junction ($L << \xi_0$), only a pair of Andreev bound states contributes to current, and analytical result is available.[4] Andreev bound states are given as $\epsilon = \pm\epsilon_0$, $\epsilon_0 = \sqrt{T}\Delta_0 cos(\phi/2)$. The corresponding current is $I = I_0 tanh(\frac{\epsilon_0}{2k_BT_B})$, $I_0(\phi) = \frac{e}{2\hbar}\sqrt{T}\Delta_0 sin(\phi/2)$ where k_B and T_B are Boltzmann constant and temperature respectively. However for the finite length junction, we mainly give numerical analysis.

Fig.1 shows the effect of junction length and impurity reflection on Andreev bound states. The length of the junction will increase the number of bound states consistent with the usual 1D quantum wells. The number can be given approximately as $2\,Int(L/(\xi_0\pi)) + 2$ or $2\,Int(L/(\xi_0\pi)) + 4$, where $Int(x)$ means the integer part of x. The symmetrical impurity ($L_1 = L/2$) opens a gap at $\phi = 2n\pi$ (n is the integer) as shown in the middle panel of Fig.1. For the asymmetrical impurity ($L_1 \neq L/2$), it can open the gap at both $\phi = 2n\pi$ and $\phi = (2n + 1)\pi$ (see the right panel of Fig.1). But the crossing point at $\phi = \pi, \epsilon = 0$ remains for arbitrary length and can not be broken by impurity scattering which is different from the conventional SNS junction.[11] That specific crossing point is protected by the fermion parity conversion.[4]

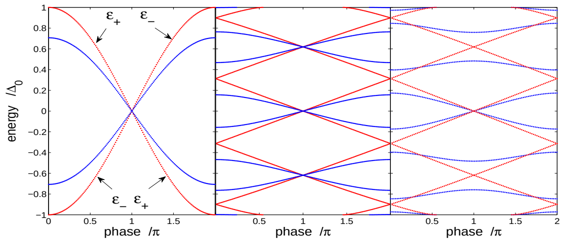

FIG. 1: (Color online) Andreev bound states with several junction length and transition coefficients. Red line T=1, blue line T=0.5. Left: $L = 0$. Middle: $L = 8\xi_0$, $L1 = L/2$. Right: $L = 8\xi_0$, $L1 = 0.2L$.

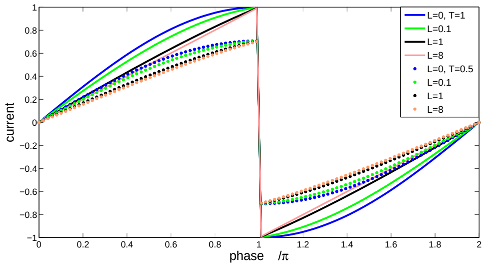

FIG. 2: (Color online) Current-phase relation for several junction length with certain transition coefficient. T=1 (0.5) for solid (dotted) line. For dotted lines the impurity distributes symmetrically. Current in unit of $\frac{ev_F}{2(L+2\xi_0)}$. Length in unit of ξ_0. Temperature is zero.

The zero temperature current-phase characteristics for different junction length and impurity strength and distribution are shown in Fig.2 and Fig.3. With the length increasing, the curve changes from sinusoidal to sawtooth. Impurity reflection is mainly to decrease the critical current. There is a robust sharp jump at $\phi = \pi$. Since the continous current is zero while $\phi = \pi$, the jump is rooted in the crossing point of Andreev bound state at $\phi = \pi, \epsilon = 0$. It will not be destroyed by impurity reflection because the impurity can not open a gap at $\phi = \pi, \epsilon = 0$, which is different from the case of conventional SNS junction.

The critical (maximum) current $I_{c,2\pi}$ is reached when $\phi = \pi$, with $I_{c,2\pi} = I_d(\pi)$ due to $I_c(\pi) = 0$. For the dirty junction

$$I_{c,2\pi}=\frac{ev_F}{2}\frac{\sqrt{T}}{\sqrt{(L+2\xi_0)^2-R(L-2L_1)^2}}. \tag{13}$$

For the clean junction $I_{c,2\pi}=\frac{1}{2}\frac{ev_F}{L+2\xi_0}$. For symmetrical impurity distribution, $I_{c,2\pi}|_T=\sqrt{T}I_{c,2\pi}|_{T=1}$. In this case, the impurity reflection monotonously decreases the critical current. The asymmetrical impurity distribution will enhance the current shown in the inset of Fig.3. That's different from the conventional SNS case where the critical current will decrease when impurity leaves the center. For the long junction with extremely asymmetrical impurity distribution ($L>>\xi_0,\ L>>L_1$), we have $I_{c,2\pi}\approx\frac{1}{2}\frac{ev_F}{L+2\xi_0}$ for T not too small, which nearly reaches the result of clean junction.

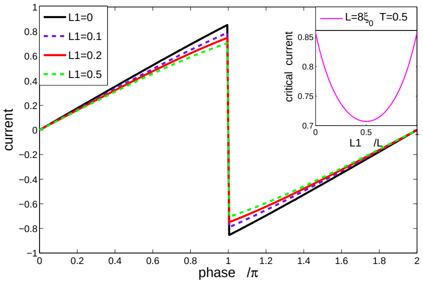

FIG. 3: (Color online) Current-phase relation for several L1. Current in unit of $\frac{ev_F}{2(L+2\xi_0)}$. L1 in unit of L. $T=0.5$, $L=8\xi_0$. Inset shows the dependence of critical current on L1. Temperature is zero.

In the previous discussion, we suppose that there is some mechanism to make quasiparticles distribute nearly thermodynamically. Now we consider the case that the necessary mechanism is absent for the two eigenstates $\varphi_\pm(\phi)$ with energy $\epsilon_\pm(\phi)$ nearest to zero shown in Fig.1. The two states are connected by electron-hole symmetry, $\varphi_+=\Xi\varphi_-$ and $\epsilon_-=-\epsilon_+$.

The original state remains while phase difference is changed adiabatically. Starting from ground state while $\phi=0$, for $\phi<2\pi$ state ϵ_- is occupied. The current due to a pair of Andreev bound states is

$$I_e=\frac{e}{\hbar}\frac{\partial\epsilon_-}{\partial\phi}f(\epsilon_-)-\frac{e}{\hbar}\frac{\partial\epsilon_-}{\partial\phi}(1-f(\epsilon_-)) \tag{14}$$

and the distribution is $f(\epsilon_-)=1$ independent of energy, then we have $I_e=\frac{e}{\hbar}\frac{\partial\epsilon_-}{\partial\phi}$ for $0<\phi<2\pi$. While $\phi=2\pi$, the system is in excited state. And it can not decay to ground state because of fermion parity conversion.[4,35] For $2\pi<\phi<4\pi$, the state ϵ_+ is occupied. While $\phi=4\pi$, the system reaches the original state we start with.[4,35] Therefore I_e is 4π periodic. The net current will be 4π periodic since I_e contributes significantly to current.

The current-phase curve is shown in Fig.4. There is a sharp jump at $\phi=2\pi$ for $I_{4\pi}$ in finite length clean junction. For $I_{2\pi}$, the jump at $\phi=\pi$ is robust against impurity reflection. However impurity reflection will make the jump located at $\phi=2\pi$ smoother for $I_{4\pi}$. The reason is that for clean junction the energy crossing of Andreev bound state at $\phi=2\pi$ has a none-zero slope. While for the dirty junction the slope is zero (see Fig.1). Here we denote the maximum of $I_{4\pi}$ ($I_{2\pi}$) as $I_{c,4\pi}=gI_{c,2\pi}$. g increases with length increasing. We have $g=1$ for the junction with length $L=0$. For the long clean junction ($L>>\xi_0$), $g=2$.[26] That's apparent if we notice that the energy level located deeply in the paring potential well is nearly linear for the long clean junction. Impurity reflection will make the factor decrease. For long junction case, vary the reflection coefficient from 0 to 1, g changes from 2 to 1. For a short junction ($L=0$), g is independent of reflection and we have $g=1$.

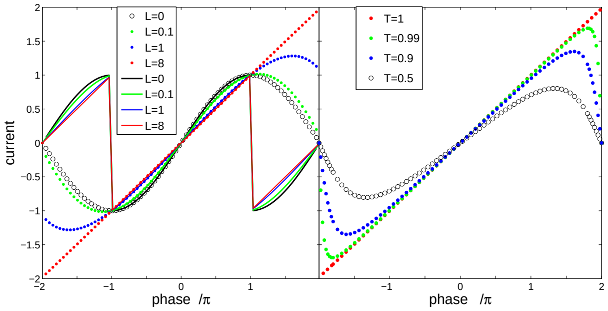

FIG. 4: (Color online) Current-phase relation to show the 4π period. Dotted (solid) line for $I_{4\pi}$ ($I_{2\pi}$). Left: T=1. Right: L=$8\xi_0$, $L_1=0.5L$. Current in unit of $\frac{ev_F}{2(L+2\xi_0)}$. Length in unit of ξ_0. Temperature is zero.

IV. CONCLUSION

In summary, the current-phase relation of a finite length STiS junction with magnetic impurity is investigated. We consider both the 2π- and 4π-period case. With the length increasing, the current-phase curve evolves form a sinusoidal shape into sawtooth shape. There is a sharp jump at $\phi=\pi$ and $\phi=2\pi$ for $I_{2\pi}$ and $I_{4\pi}$ respectively in the clean junction. For $I_{2\pi}$, the sharp jump at $\phi=\pi$ is robust against impurity strength and distribution. However for $I_{4\pi}$, the impurity makes the jump at $\phi=2\pi$ smooth. The critical current is greatly influenced by junction length and impurity.

ACKNOWLEDGMENTS

This work was financially supported by NBRP of China (2012CB921303 and 2009CB929100) and NSF-China under Grants Nos. 11074174 and 11274364. One of the authors (S.F.Zhang) wishes to thank H.W.Liu and S.N.Zhang for helpful discussions.

Appendix A

This appendix explains the origin of the similarity and difference between the STiS junction and conventional SNS junction.

For the SNS junction, Nambu basis can be selected in two equivalent form, $\psi_+ = (\psi_\uparrow, \psi_\downarrow^\dagger)^T$ or $\psi_- = (\psi_\downarrow, \psi_\uparrow^\dagger)^T$, due to spin degeneracy. With $i\hbar\partial_t\psi_\pm = H_{BdG}\psi_\pm$, we can derive $H_{BdG} = (p_x^2/2m - \mu)\tau_3 + \Delta_0[cos(\phi')\tau_1 - sin(\phi')\tau_2]$, $p_x = -i\hbar\partial_x$ and m is the effective mass of electron. Take the Andreev approximation[30,36] and denote the eigenvector as $\varphi = \chi e^{i(\sigma k_F + \delta k)\,x}$, $\sigma = \pm$ for incident particles with wave vector near $\pm k_F$, χ is a vector independent of x. Then we arrive at the Andreev equation[30]

$$\begin{pmatrix} \sigma v_F p_x - \hbar v_F k_F & \Delta \\ \Delta^* & -\sigma v_F p_x + \hbar v_F k_F \end{pmatrix} \varphi = \epsilon\,\varphi \quad (15)$$

If we reset Nambu basis as $\Psi' = (\psi_\uparrow, \psi_\downarrow, \psi_\downarrow^\dagger, \psi_\uparrow^\dagger)^T$ and take $\sigma = 1(-1)$ for $\psi_+(\psi_-)$, we will find the corresponding BdG Hamiltonian is identical to the BdG Hamiltonian of STiS junction, but the Nambu basises are connected with a unitary transformation $P = \begin{pmatrix} \sigma_0 & \\ & \sigma_3 \end{pmatrix}$, in which σ_0 is a 2×2 unit matrix. P matrix leads that for dirty STiS junction there will be an extra π phase shift for hole reflection as is shown in Eq.(3). The other choice to take $\sigma = 1(-1)$ for $\psi_-(\psi_+)$ corresponds to the same junction formed on the other side of the 2D TI.

Appendix B

This appendix is to derive the current formula Eq.(7) and give some detail of calculating the current.

The system is given as

$$H \;=\; \int dx \psi^\dagger (H_0 - \mu)\psi + \Delta\psi_\uparrow^\dagger\psi_\downarrow^\dagger + \Delta^*\psi_\downarrow\psi_\uparrow \quad (16)$$

With $i\hbar\partial_t\Psi = H_{BdG}\Psi$, the BdG Hamiltonian is yielded

$$H_{BdG} = \begin{pmatrix} H_0 - \mu & \Delta \\ \Delta^* & -\hat{T}(H_0 - \mu)\hat{T}^{-1} \end{pmatrix} \quad (17)$$

with time reversal operator $\hat{T} = -i\sigma_2 K$. In fact Eq.(17) is appropriate for arbitrary H_0 but with the corresponding time reversal operator for different systems. The BdG equation can be written as

$$H_{BdG}\;\varphi_{i,\nu}(x) = \epsilon_{i,\nu}\,\varphi_{i,\nu}(x) \quad (18)$$

where $\varphi_{i,\nu} = (u_{i,\nu}(x), u'_{i,\nu}(x), v_{i,\nu}(x), v'_{i,\nu}(x))^T$ is the eigenvector and $\epsilon_{i,\nu}$ is the eigenvalue. Because of electron-hole symmetry $\{H_{BdG}, \Xi\} = 0$, $\Xi\varphi_{i,\nu}(x)$ is also an eigenvector with eigenvalue $-\epsilon_{i,\nu}$. ν and i denote energy and the extra degeneracy respectively. For continuous spectrum $i = 1, 2, 3, 4$, $\varphi_{3,\nu} = \Xi\varphi_{2,\nu}, \varphi_{4,\nu} = -\Xi\varphi_{1\nu}$. $\varphi_{i,\nu}$ is the scattering state constructed from the incident state (eigenstate of 1D TS) $\tilde{\varphi}_{i,\nu}$ shown in Fig.5. However for Andreev bound states we only have $i = \pm$, $\varphi_{-,\nu} = \Xi\varphi_{+,\nu}$. For simplicity we denote $\varphi_{-,\nu} = \varphi_{1,\nu}$, $\varphi_{+,\nu} = \varphi_{4,\nu}$ and $\varphi_{2,\nu} = \varphi_{3,\nu} = 0$.

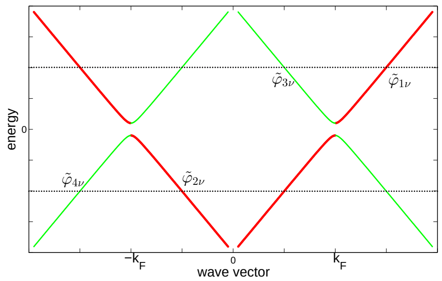

FIG. 5: (Color online) Continuous energy spectrum for infinite 1D TS. Red and green lines correspond to electronlike and holelike eigenstates of 1D TS respectively. $\tilde{\varphi}_{i\nu}$ is the the incident state from which one can construct the scattering state $\varphi_{i\nu}$.

To diagonalize the Hamiltonian we first rewrite it as $H = \frac{1}{2}\int dx \Psi^\dagger H_{BdG}\Psi + constant$. The Bogoliubov transformation is given as $\Psi = \sum_\nu S_\nu\gamma_\nu$, in which $S_\nu = (\varphi_{1,\nu}, \varphi_{2,\nu}, \varphi_{3,\nu}, \varphi_{4,\nu})$, $\gamma_\nu = (\gamma_{1,\nu}, \gamma_{2,\nu}, \gamma_{3,\nu}, \gamma_{4,\nu})^T$, $\gamma_{4,\nu} = -\gamma_{1,\nu}^\dagger$, $\gamma_{3,\nu} = \gamma_{2,\nu}^\dagger$. $\gamma_{i\nu}$ annihilates a quasiparticle in eigenstate $\varphi_{i\nu}$. Then we have $H = \frac{1}{2}\sum_{i,\nu}\epsilon_{i,\nu}\gamma_{i,\nu}^\dagger\gamma_{i,\nu} + constant$.

The current density operator can be derived with the current density conversion equation, $\partial_t\hat{\rho}(x) + \partial_x\hat{J}(x) = 0$, in which electron density operator $\hat{\rho}(x) = e(\psi_\uparrow^\dagger(x)\psi_\uparrow(x) + \psi_\downarrow^\dagger(x)\psi_\downarrow(x))$. In the TI region, it can be derived as $\hat{J}(x) = ev_F(\psi_\uparrow^\dagger(x)\psi_\uparrow(x) - \psi_\downarrow^\dagger(x)\psi_\downarrow(x))$. In the TS region, the paring potential will contribute an additional term $-\partial_x\hat{J}_s = 2e(\Delta\psi_\uparrow^\dagger\psi_\downarrow^\dagger - H.C.)/i\hbar$, which describes exchanging Cooper pairs between quasiparticles and condensate. However this term vanishes for energy larger than paring potential, thus it makes no contribution to the continuous current. But it will make the discrete current transforms into supercurrent carried by the condensate gradually in the superconducting region.[37]

Take the ensemble average $J(x) = <\hat{J}(x)>$, with Bogoliubov transformation and $<\gamma_{i,\nu}^\dagger\gamma_{i,\nu}> = f(\epsilon_{i,\nu})$. In the TI region we find $J = \sum_\nu J_{1,\nu} + J_{2,\nu}$,

$$\begin{aligned} J_{i,\nu} = \;& ev_F\;\;[|u_{i,\nu}|^2 f(\epsilon_{i,\nu}) - |v_{i,\nu}|^2(1 - f(\epsilon_{i,\nu}))] \\ -\;& \;[|u'_{i,\nu}|^2 f(\epsilon_{i,\nu}) - |v'_{i,\nu}|^2(1 - f(\epsilon_{i,\nu}))] \quad (19) \end{aligned}$$

which is just Eq.(7) we want to derive. The extra current owing to paring potential is $< -\partial_x\hat{J}_s > = \frac{4ev_F}{\hbar}Im\{\Delta\sum_{i=1,2;\nu}[u_{i,\nu}^* v_{i,\nu} f(\epsilon_{i,\nu}) - u'^*_{i,\nu}v'_{i,\nu}f(\epsilon_{i,\nu})]\}$.

Now we prove that the contributions from electronlike and holelike injected states are equal. $J_{e,\nu}$ ($J_{h,\nu}$) is the current due to electronlike (holelike) state $\varphi_{e,\nu}$ ($\varphi_{h,\nu}$) with eigenvalue $\epsilon_{e,\nu}$ ($\epsilon_{h,\nu}$) where $e = \{1, 2\}$, $h = \{3, 4\}$.

$J_{e/h,\nu}$ is given by Eq.(19). Since $\varphi_{h,\nu} = \Xi\varphi_{e,\nu}$, $\epsilon_{h,\nu} = -\epsilon_{e,\nu}$ and $1 - f(\epsilon) = f(-\epsilon)$, we can obtain $J_{e,\nu} = J_{h,\nu}$.

For continuous spectrum, the eigenstate with a certain energy is 4-fold degenerate. The continuous current can be written as, $I_c = \int d\epsilon_\nu N(\epsilon_\nu) J(\epsilon_\nu)/2$, $J(\epsilon_\nu) = \sum_i J_i(\epsilon_{i\nu}) = ev_F[\sum_i(|u_{i,\nu}|^2 + |v_{i,\nu}|^2 - |u'_{i,\nu}|^2 - |v'_{i,\nu}|^2) f(\epsilon_{i,\nu}) - \sum_i |v_{i,\nu}|^2 + \sum_i |v'_{i,\nu}|^2]$, $N(\epsilon_\nu)$ is the density of states of TS. Solve the eigenvectors and we find the last two terms cancel with each other. Then we have $I_c = -\frac{1}{2}\int d\epsilon_\nu N(\epsilon_\nu)[J'_1(\epsilon_\nu) + J'_2(\epsilon_\nu)] tanh(\frac{\epsilon_\nu}{2k_B T_B})$, where $J'_i(\epsilon_\nu) = ev_F(|u_{i,\nu}|^2 + |v_{i,\nu}|^2 - |u'_{i,\nu}|^2 - |v'_{i,\nu}|^2)$, which is the equation we use to derive Eqs. (10)-(12).

Appendix C

This appendix is to prove the discrete current obtained by wave function method and quantum statistical method is identical if the states are occupied thermodynamically.[38]

In this appendix we take the Nambu basis given as $\Psi' = (\psi_\uparrow, \psi^\dagger_\downarrow, \psi_\downarrow, -\psi^\dagger_\uparrow)^T$ for simplicity. The corresponding BdG Hamiltonian is

$$H'_{BdG} = \begin{pmatrix} (v_F p_x - \mu)\tau_3 + \hat{\Delta} & M(x)\tau_0 \\ M(x)\tau_0 & (-v_F p_x - \mu)\tau_3 + \hat{\Delta} \end{pmatrix} \quad (20)$$

where $M(x) = M\theta(x - L_1)\theta(L_2 - x)$, τ_0 is a 2×2 unit matrix and $\hat{\Delta} = \begin{pmatrix} & \Delta_0 e^{i\phi sgn(x)/2} \\ \Delta_0 e^{-i\phi sgn(x)/2} & \end{pmatrix}$, $sgn(x) = x/|x|$.

A pair of Andreev bound states connected by electron-hole transformation is given as $\varphi'_\pm$ with energy $\epsilon_\pm$, $\varphi'_+ = \Xi\varphi'_-$, $\varphi'_\pm = (u_\pm(x), v_\pm(x), u'_\pm(x), v'_\pm(x))^T$ and $\epsilon_- = -\epsilon_+$. The corresponding current is $J = ev_F(|u_-|^2 + |v_-|^2 - |u'_-|^2 - |v'_-|^2)(f(\epsilon_-) - f(\epsilon_+))/2 + ev_F(|u_-|^2 - |v_-|^2 - |u'_-|^2 + |v'_-|^2)/2$. With the solved eigenvectors, we find the second term on the right side vanishes. Then the current is derived as

$$J = I(\epsilon_-)f(\epsilon_-) + I(\epsilon_+)f(\epsilon_+), \quad (21)$$

in which $I(\epsilon_\pm) = ev_F(|u_\pm|^2 + |v_\pm|^2 - |u'_\pm|^2 - |v'_\pm|^2)/2$ and $I(\epsilon_+) = -I(\epsilon_-)$. $I(\epsilon_\pm)$ can be seen as the effective current carried by eigenstate $\varphi'_\pm$.

Rewrite the current as $J = I(\epsilon_-)(f(\epsilon_-) - f(\epsilon_+))$, and then act the operator $p_x = -i\hbar\partial_x$ on both sides. With a straightforward calculation, we have $2p_x J/e = \varphi'^\dagger_- \begin{pmatrix} [\hat{\Delta}, \tau_3] & \\ & [\hat{\Delta}, \tau_3] \end{pmatrix} \varphi'_- \cdot (f(\epsilon_-) - f(\epsilon_+))$. With $[\hat{\Delta}, \tau_3] = 4isgn(x)\frac{\partial\hat{\Delta}}{\partial\phi}$, we derive $\frac{-\hbar}{2e} sgn(x)\partial_x J = \varphi'^\dagger_- \frac{\partial H_{BdG}}{\partial\phi}\varphi'_-(f(\epsilon_-) - f(\epsilon_+))$. Integrate among the the whole region. Since the current in the TI region is constant and it decays to zero gradually in the superconductor, the left side gives $\hbar J(x = 0)/e$. With the help of Feynman-Hellmann theorem the right side gives $\frac{\partial\epsilon_-}{\partial\phi}(f(\epsilon_-) - f(\epsilon_+))$. Then we obtain

$$J = \frac{e}{\hbar}\frac{\partial\epsilon_-}{\partial\phi}f(\epsilon_-) + \frac{e}{\hbar}\frac{\partial\epsilon_+}{\partial\phi}f(\epsilon_+). \quad (22)$$

Comparing with Eq.(21) we have $I(\epsilon_\pm) = \frac{e}{\hbar}\frac{\partial\epsilon_\pm}{\partial\phi}$. So far we have proved the two methods are equivalent for the discrete current.

It's of importance to point out that the quantum statistical method has taken both particle energy levels and hole energy levels into consideration. For a clean STiS junction with length $L = 0$, one can take the Nambu basis to be $\psi = (\psi_\uparrow, \psi^\dagger_\downarrow)^T$ and the corresponding BdG Hamiltonian is 2×2. In this case there is only one energy level with energy $\epsilon_-(\phi)$ contributes to current. However as we have discussed a wrong result, $J = \frac{e}{\hbar}\frac{\partial\epsilon_-}{\partial\phi}f(\epsilon_-)$, will be derived if we use the quantum statistical method .

---

[*] Electronic address: sunqf@iphy.ac.cn

[1] X. L. Qi and S. C. Zhang, Rev.Mod.Phys. **83**, 1057 (2010).
[2] M. Z. Hasan and C. L. Kane, Rev. Mod. Phys. **82**, 3045 (2010).
[3] L. Fu and C. L. Kane, Phys.Rev.Lett. **100**,096407(2008).
[4] L. Fu and C. L. Kane, Phys.Rev.B **79**, 161408(R)(2009).
[5] M. König, S. Wiedmann, C. Brüne, A. Roth, H. Buhmann, L. W. Molenkamp, X.-L. Qi, and S.-C. Zhang, Science **318**, 766 (2007).
[6] I. Knez, R.-R. Du, and G. Sullivan, Phys.Rev.Lett. **107**, 136603 (2011).
[7] Y. Xia, D. Qian, D. Hsieh, L. Wray, A. Pal, H. Lin, A. Bansil, D. Grauer, Y. S. Hor, R. J. Cava, and M. Z. Hasan, Nat.Phys. **5**, 398 (2009).
[8] I. Knez, R.-R. Du, and G. Sullivan, Phys. Rev. Lett. **109**, 186603 (2012).
[9] M.-X. Wang, C.-H. Liu, J.-P. Xu, F. Yang, L. Miao, M.-Y. Yao, C. L. Gao, C.-Y. Shen, X.-C. Ma, X. Chen, Z.-A. Xu, Y. Liu, S.-C. Zhang, D. Qian, J.-F. Jia, and Q.-K. Xue, Science **336**, 52 (2012).
[10] I.O. Kulik, Zh. Eksp. Teor. Fiz. **57**, 1745 (1969) [Sov. Phys. JETP **30**, 944 (1970)].
[11] P.F. Bagwell, Phys.Rev. B **46** 12573 (1992).
[12] D. Averin and A. Bardas, Phys. Rev. Lett. **75**, 1831 (1995).
[13] M.Hurd, S. Datta, and P.F. Bagwell, Phys.Rev.B **56**, 11232 (1997).
[14] A. A. Golubov, M. Yu. Kupriyanov, and E. Ilichev, Rev. Mod. Phys **76** 411 (2004).
[15] For Andreev bound states there is a difference of degeneracy. For $I_{2\pi}(\phi)$ there is a difference of factor 2.
[16] A.Y.Kitaev Phys.Usp. **44** 131 (2001).
[17] D.M. Badiane, M. Houzet, and J.S. Meyer, Phys.Rev.Lett. **107**, 177002 (2011).
[18] H. -J. Kwon, K. Sengupta, and V. M. Yakovenko, Eur. Phys. J. B **37**, 349 (2004).
[19] R.M. Lutchyn, J.D. Sau, and S.D. Sarma, Phys.Rev.Lett.

105, 077001 (2010).

[20] K.T. Law and P.A. Lee, Phys.Rev.B **84**, 081304 (2011).

[21] P. A. Ioselevich and M.V. Feigelman, Phys.Rev.Lett.**106**, 077003 (2011).

[22] F. S. Nogueira and I. Eremin, J.Phys.Condens.Matter **24**, 325701 (2012).

[23] P. San-Jose, E. Prada, and R. Aguado, Phys.Rev.Lett. **108**, 257001 (2012).

[24] F. DomÍnguez, F. Hassler, and G. Platero, Phys.Rev.B **86**,140503(R) (2012).

[25] D. I. Pikulin and Yu. V. Nazarov, Phys. Rev. B **86**, 140504 (R) (2012).

[26] C.W.J. Beenakker, D.I. Pikulin, T. Hyart, H. Schomerus, and J.P. Dahlhaus, Phys.Rev.Lett. **110**, 017003 (2013).

[27] The effect of the other side is neglected because of large space difference.

[28] P. G. de Gennes, *Superconductivity of Metals and Alloys* (Addison-Wesley, New York, 1989).

[29] For SNS junction $S_h(-\epsilon) = S_e^*(\epsilon)$.

[30] A.F.Andreev, Sov.Phys.JETP **19**, 1228 (1964).

[31] P. Adroguer, C. Grenier, D. Carpentier, J. Cayssol, P. Degiovanni, and E. Orignac, Phys. Rev. B **82**, 081303(R) (2010).

[32] Q.-F. Sun, Y.-X. Li, W. Long, and J. Wang, Phys. Rev. B **83**, 115315 (2011).

[33] A.A. Abrikosov, *Theory of Metals* (North-Holland, Amsterdam, 1988).

[34] S. Datta, P. F. Bagwell, and M. P. Anantram, Phys.Low-Dimens.Struct. **3**, 1 (1996).

[35] J. Alicea, Rep.Prog.Phys. **75**, 076501 (2012).

[36] Andreev approximation means $\mu >> |\Delta|$, the dispersion curve is approximated to be linear near $\pm k_F$.

[37] G. E. Blonder, M. Tinkham, and T. M. K.lapwijk, Phys. Rev. B **25**, 4515 (1982).

[38] V. S. Shumeiko, E. N. Bratus, and G. Wendin, Low. Temp. Phys. **23**, 181 (1997).